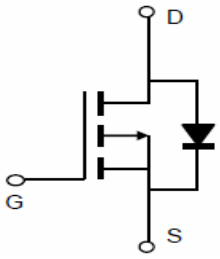
EFMICRO
Semiconductor Limited Company

EFM2317/A

P-Channel Advanced Power MOSFET

• Product Summary

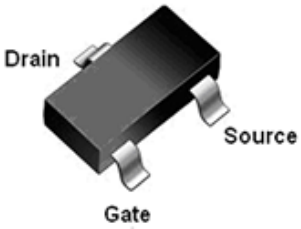
Part #	V_{DS}	$R_{DS(on).typ}$ ($@V_{GS}$=4.5V)	$R_{DS(on).typ}$ ($@V_{GS}$=2.5V)	I_D
EFM2317/A	-20V	17mΩ	22mΩ	-6A



P-Channel MOSFET

• Description

■ The EFM2317/A uses advanced trench technology to provide
■ excellent $R_{DS(ON)}$, low gate charge and operation with gate
■ voltages as low as 2.5V. This device is suitable for use as a
■ load switch or in PWM applications.



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•Application

■ PWM applications
■ Load switch
■ Power management
■ Halogen-free

•Ordering Information:

Part NO.	EFM2317	EFM2317A
Marking	2317	2317A
Packing Information	SOT-23L	SOT23-3L
Basic ordering unit (pcs)	3000	

•Absolute Maximum Ratings (T_C=25℃)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	±12	V
Drain Current-Continuous	I_D	-6	A
Drain Current-Pulsed (Note 1)	I_{DM}	-24	A
Maximum Power Dissipation	P_D	1.8	W
Operating Junction and Storage Temperature Range	T_J,T_{STG}	-55 To 150	℃

•Thermal Characteristic

Thermal Resistance,Junction-to-Ambient (Note 2)	$R_{\theta JA}$	69	℃/W

● Static Electrical Characteristics @ T_J = 25°C (unless otherwise stated)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=250uA	-20	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-16V V_{GS}=0V	--	--	-1	uA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±12V V_{DS}=0V	--	--	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS} I_D=250uA	-0.4	-0.6	-1.0	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=-4.5V I_D=-6A	--	17	20	mΩ
		V_{GS}=-2.5V I_D=-5A	--	22	30	mΩ
Dynamic Characteristics (Note4)						
Input Capacitance	C_{lss}	V_{DS}=-20V V_{GS}=0V F=1.0MHz	--	1030	--	PF
Output Capacitance	C_{oss}		--	120	--	PF
Reverse Transfer Capacitance	C_{rss}		--	105	--	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=-10V I_D=-6A V_{GS}=-4.5V R_G=3.3Ω,	--	10	--	nS
Turn-on Rise Time	t_r		--	18	--	nS
Turn-Off Delay Time	$t_{d(off)}$		--	23.	--	nS
Turn-Off Fall Time	t_f		--	31	--	nS
Total Gate Charge	Q_g	V_{DS}=-10V I_D=-6A V_{GS}=-4.5V	--	13	--	nC
Gate-Source Charge	Q_{gs}		--	1.8	--	nC
Gate-Drain Charge	Q_{gd}		--	4.7	--	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	V_{GS}=0V I_S=-1.2A	--	-0.84	-1.2	V
Diode Forward Current (Note 2)	I_S		--	--	-6	A

Notes:

① Pulse width limited by maximum allowable junction temperature

②Pulse test ; Pulse width≤300μs, duty cycle≤2%.

• Typical Characteristics

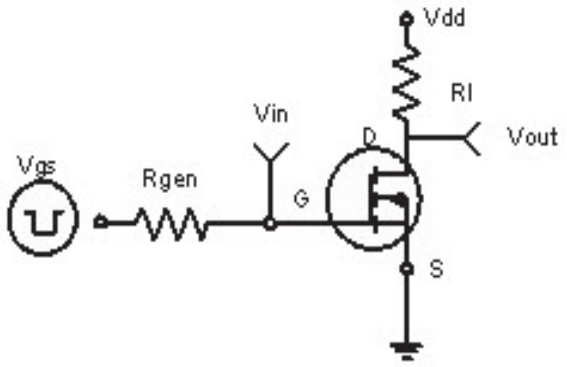


Figure 1:Switching Test Circuit

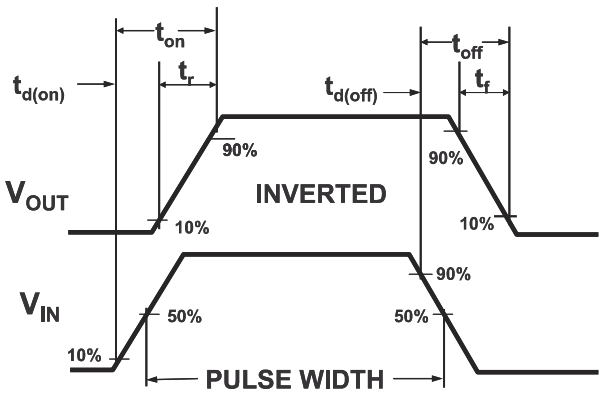


Figure 2:Switching Waveforms

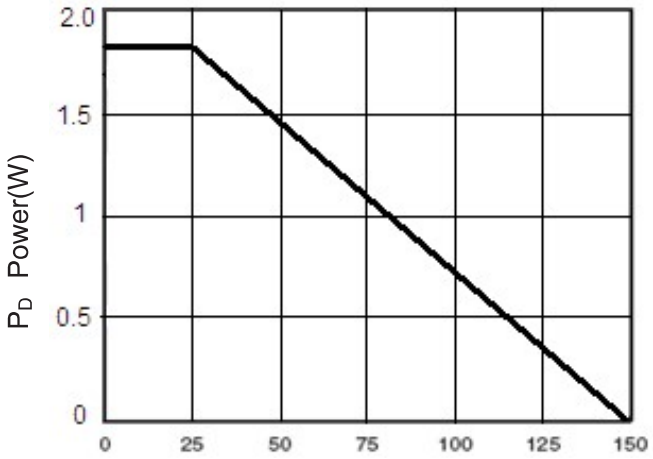


Figure 3 Power Dissipation

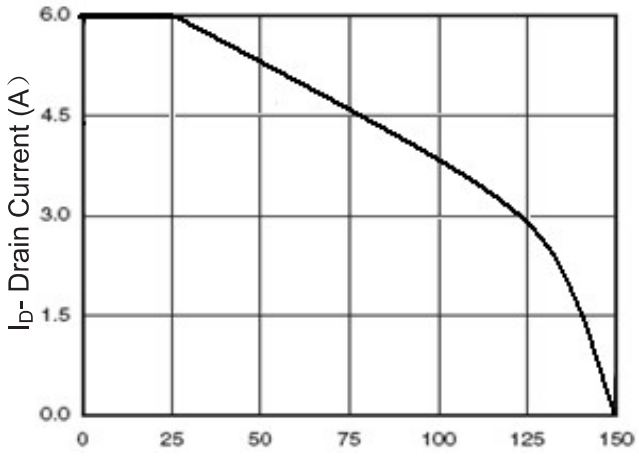


Figure 4 Drain Current

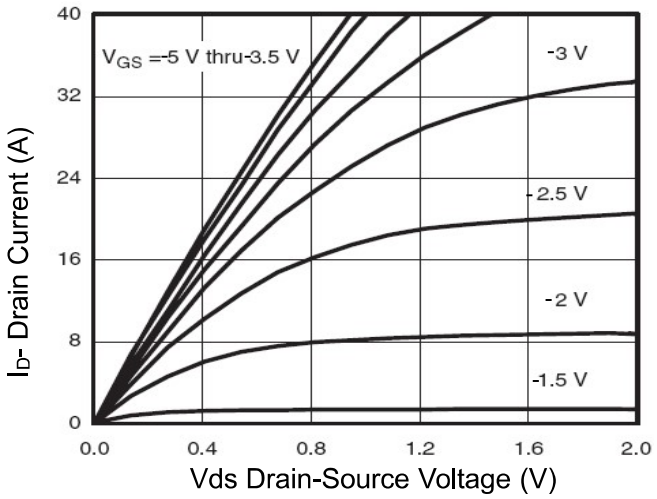


Figure 5 Output Characteristics

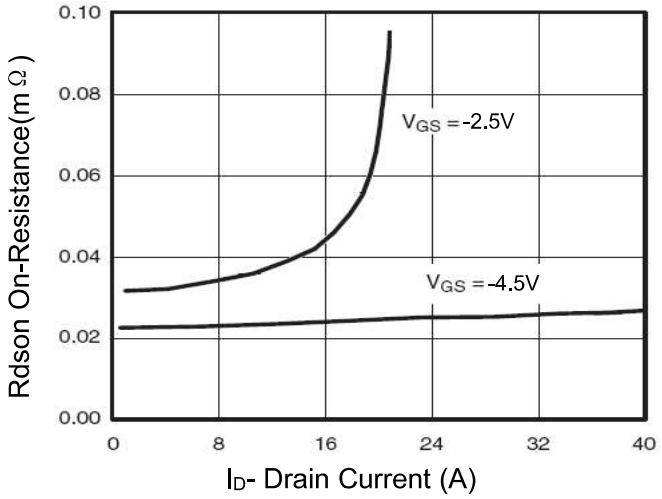


Figure 6 Drain-Source On-Resistance

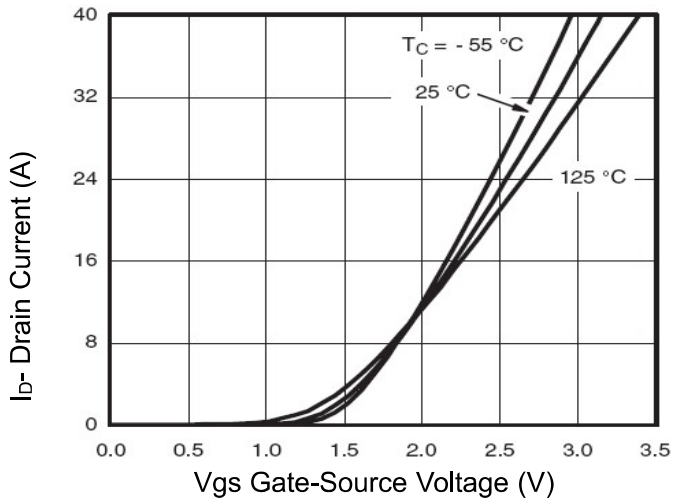


Figure 7 Transfer Characteristics

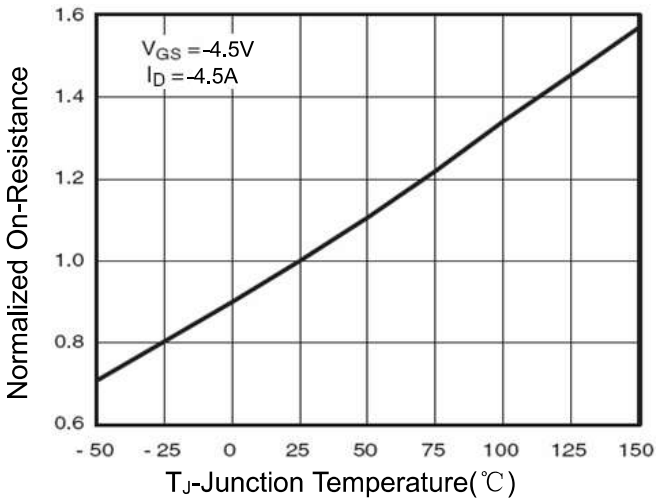


Figure 8 Drain-Source On-Resistance

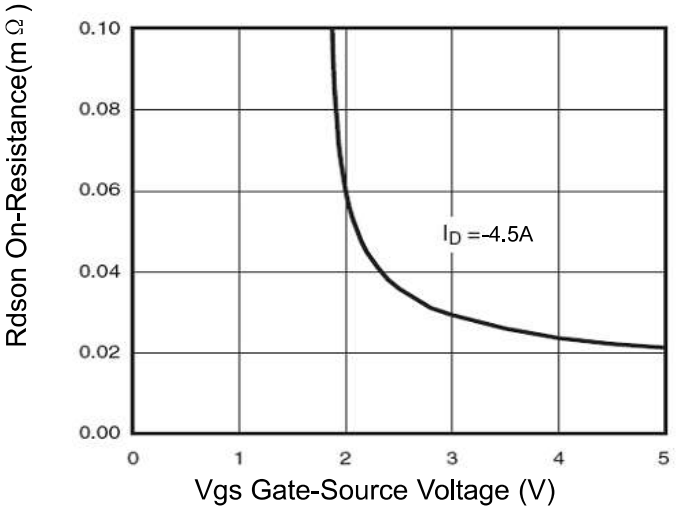


Figure 9 Rdson vs Vgs

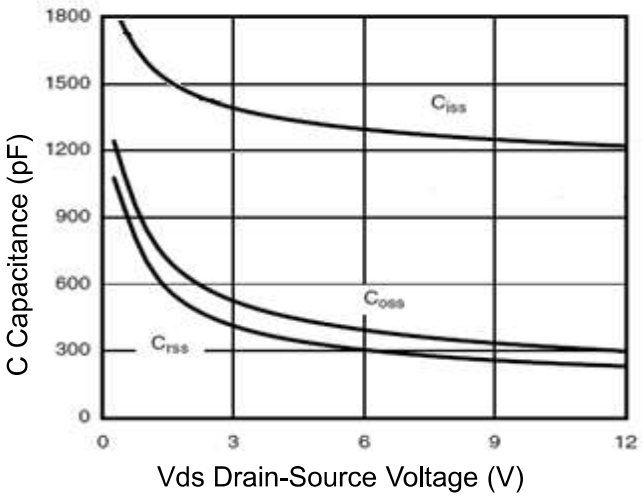


Figure 10 Capacitance vs Vds

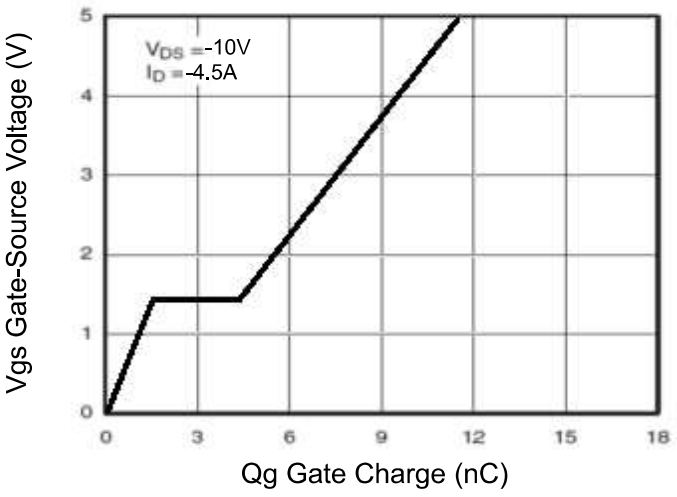


Figure 11 Gate Charge

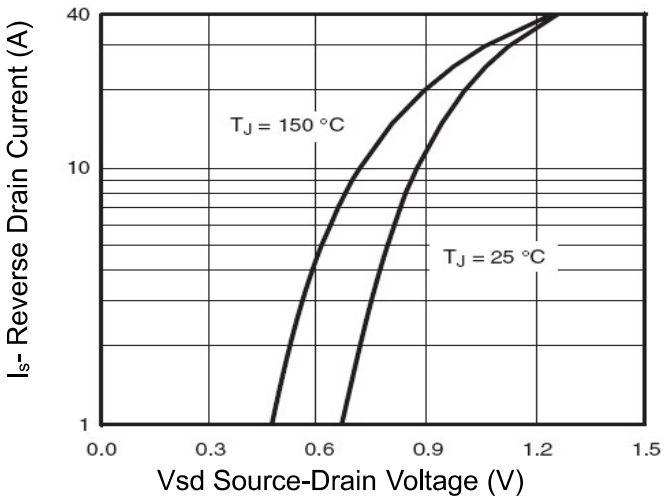


Figure 12 Source- Drain Diode Forward

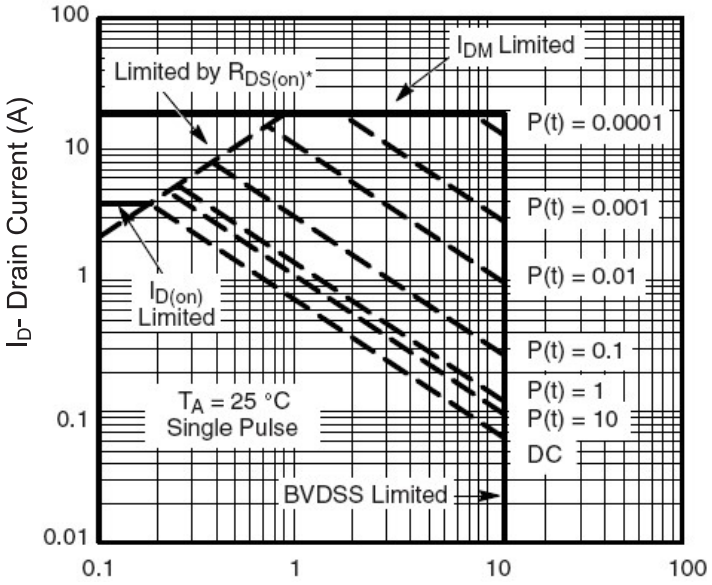


Figure 13 Safe Operation Area

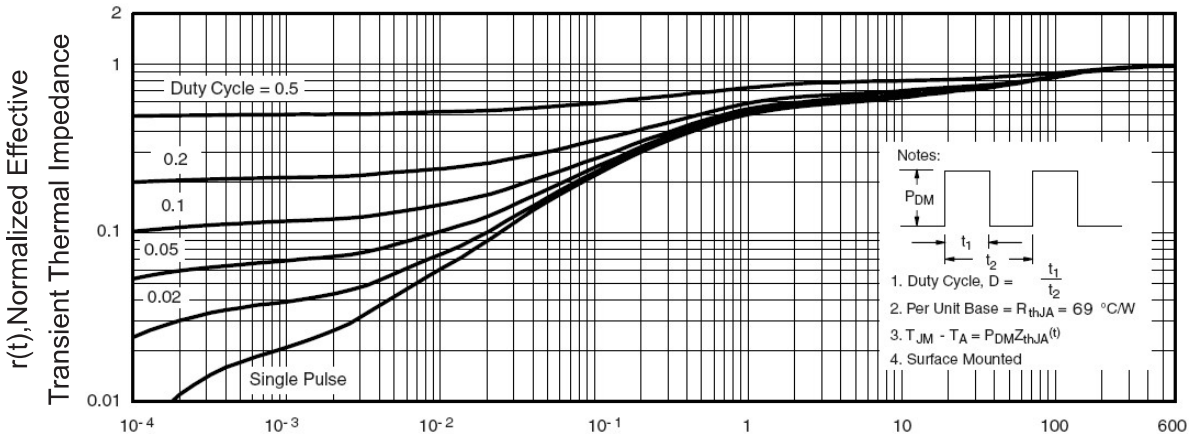
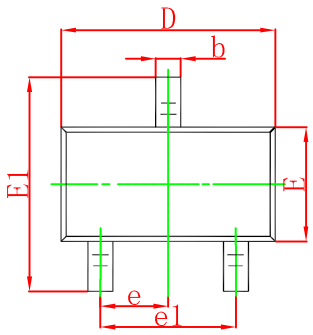
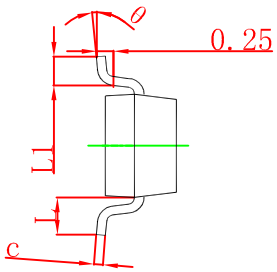
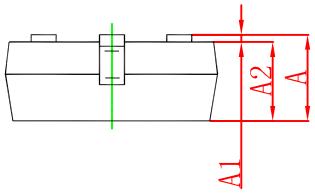


Figure 14 Normalized Maximum Transient Thermal Impedance

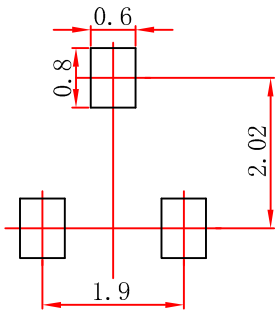
SOT-23 Package Outline Dimensions







Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°



Note:
1.Controlling dimension:in millimeters.
2.General tolerance:± 0.05mm.
3.The pad layout is for reference purposes only.